GB01SLT12-252

1200V 1A SiC Schottky MPS™ Diode

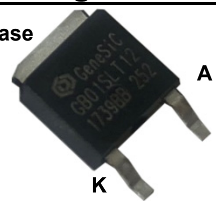
Silicon Carbide Schottky Diode

V_{RRM}	=	1200 V
$I_{F\ (Tc\ =\ 135°C)}$	=	3 A
Q_C	=	3 nC

Features

- High Avalanche (UIS) Capability
- Enhanced Surge Current Capability
- Superior Figure of Merit Q_C/I_F
- Low Thermal Resistance
- 175 °C Maximum Operating Temperature
- Temperature Independent Switching Behavior
- Positive Temperature Coefficient of V_F
- Extremely Fast Switching Speeds

Package



TO-252-2

Advantages

- Low Standby Power Losses
- Improved Circuit Efficiency (Lower Overall Cost)
- Low Switching Losses
- Ease of Paralleling without Thermal Runaway
- Smaller Heat Sink Requirements
- Low Reverse Recovery Current
- Low Device Capacitance
- Low Reverse Leakage Current

Applications

- Boost Diode in Power Factor Correction (PFC)
- Switched Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Motor Drives
- Freewheeling / Anti-parallel Diode in Inverters
- Solar Inverters & Wind Energy Converters
- Electric Vehicles (EV) & DC Fast Charging
- Induction Heating & Welding

Absolute Maximum Ratings (At T_C = 25 °C Unless Otherwise Stated)

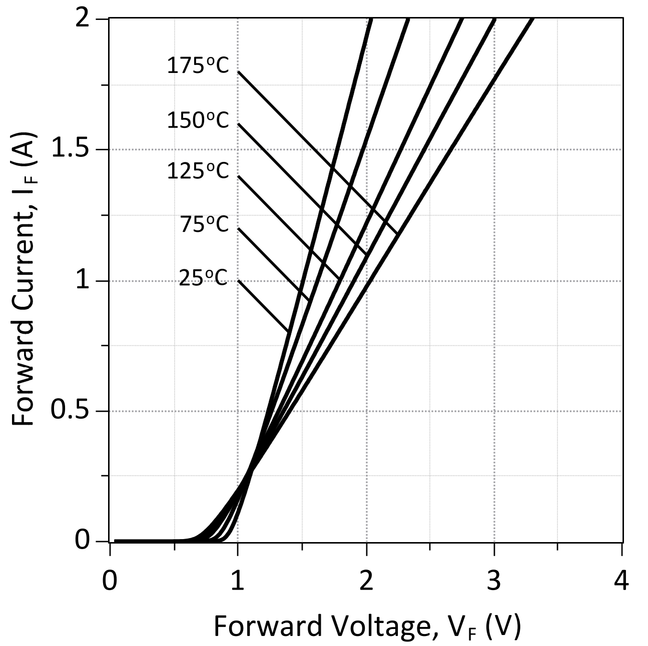
Parameter	Symbol	Conditions	Values	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
Continuous Forward Current	I_F	T_C = 25 °C, D = 1	7	A
		T_C = 135 °C, D = 1	3	
		T_C = 170°C, D = 1	1	
Non-Repetitive Peak Forward Surge Current, Half Sine Wave	$I_{F,SM}$	T_C = 25 °C, t_P = 10 ms	8	A
		T_C = 150 °C, t_P = 10 ms	7	
Repetitive Peak Forward Surge Current, Half Sine Wave	$I_{F,RM}$	T_C = 25 °C, t_P = 10 ms	5	A
		T_C = 150 °C, t_P = 10 ms	4	
Non-Repetitive Peak Forward Surge Current	$I_{F,max}$	T_C = 25 °C, t_P = 10 µs	40	A
i^2t Value	$\int i^2\,dt$	T_C = 25 °C, t_P = 10 ms	0.3	A^2s
Non-Repetitive Avalanche Energy	E_{AS}	L = 48 mH, I_{AS} = 1 A	24	mJ
Diode Ruggedness	dV/dt	V_R = 0 ~ 960 V	200	V/ns
Power Dissipation	P_{tot}	T_C = 25 °C	60	W
Operating and Storage Temperature	T_j , T_{stg}		-55 to 175	°C

Electrical Characteristics

Parameter	Symbol	Conditions		Values Min.	Values Typ.	Values Max.	Unit
Diode Forward Voltage	V_F	I_F = 1 A, T_j = 25 °C			1.5	1.8	V
		I_F = 1 A, T_j = 175 °C			2	2.4	
Reverse Current	I_R	V_R = 1200 V, T_j = 25 °C			0.2	1	μA
		V_R = 1200 V, T_j = 175 °C			2	10	
Total Capacitive Charge	Q_C	$I_F \leq I_{F,MAX}$, dI_F/dt = 200 A/μs, T_j = 175 °C	V_R = 400 V		2		nC
			V_R = 800 V		3		
Switching Time	t_s		V_R = 400 V		< 10		ns
			V_R = 800 V				
Total Capacitance	C	V_R = 1 V, f = 1 MHz			78		pF
		V_R = 800 V, f = 1 MHz			5		

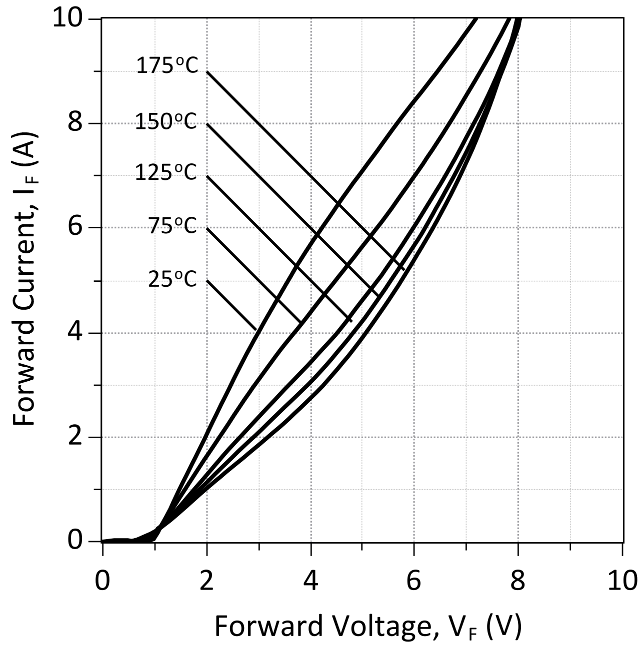
Thermal / Mechanical Characteristics

Thermal Resistance, Junction - Case	R_{thJC}	2.52	°C/W
Weight	W_T	0.3	g



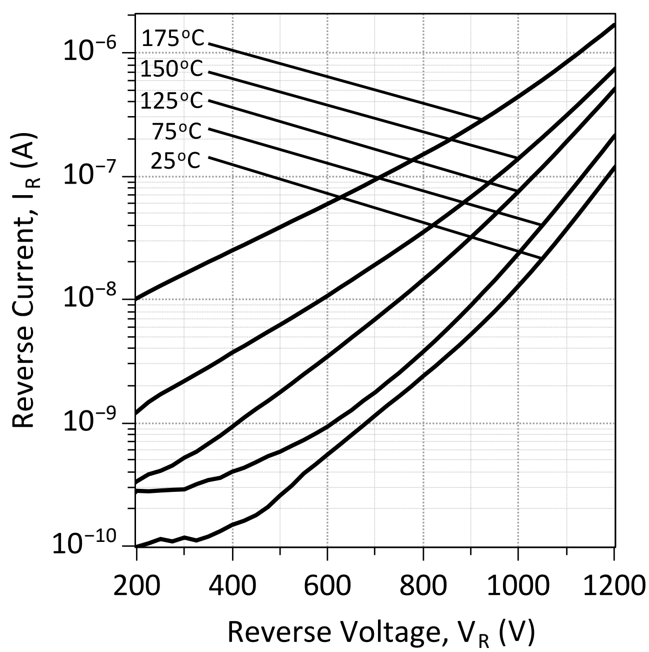
$I_F = f(V_F, T_j)$; t_P = 250 µs

Figure 1: Typical Forward Characteristics



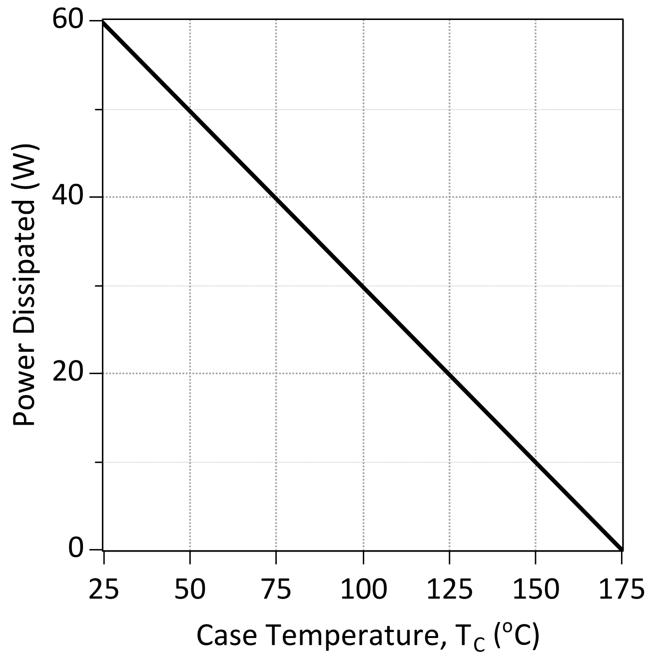
$I_F = f(V_F, T_j)$; t_P = 250 µs

Figure 2: Typical High Current Forward Characteristics



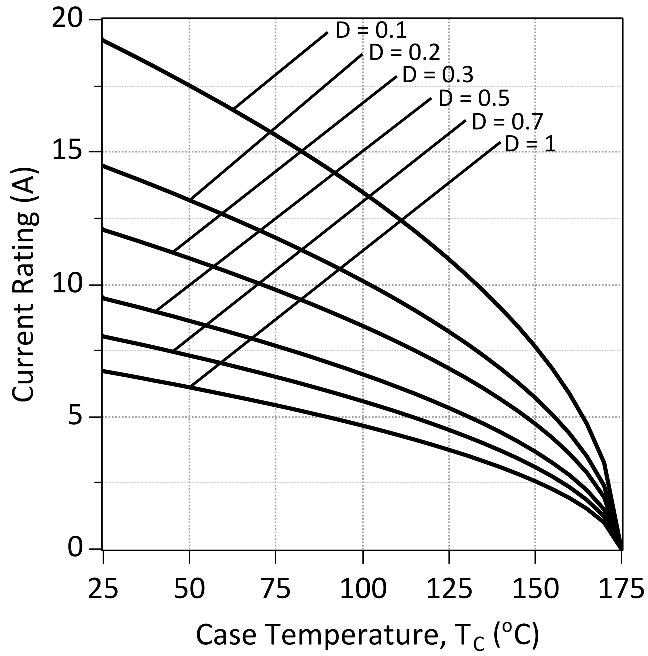
$I_R = f(V_R, T_j)$

Figure 3: Typical Reverse Characteristics



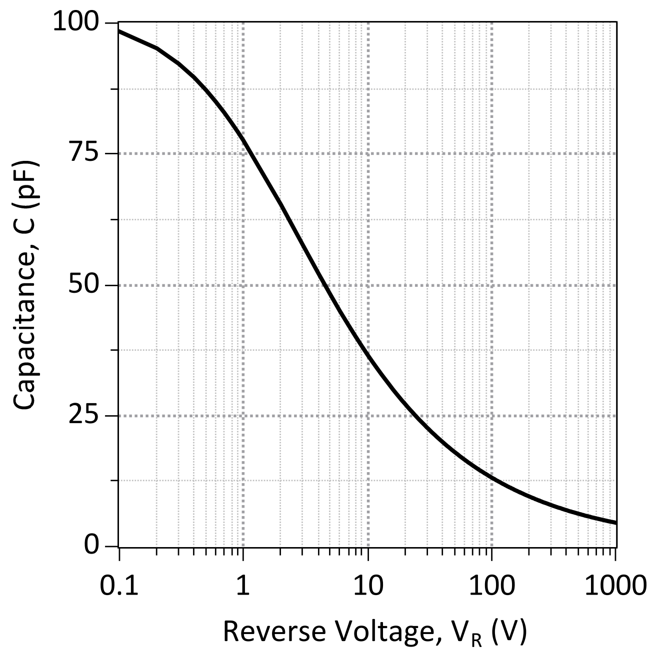
$P_{tot} = f(T_C)$; T_j = 175 °C

Figure 4: Power Derating Curve



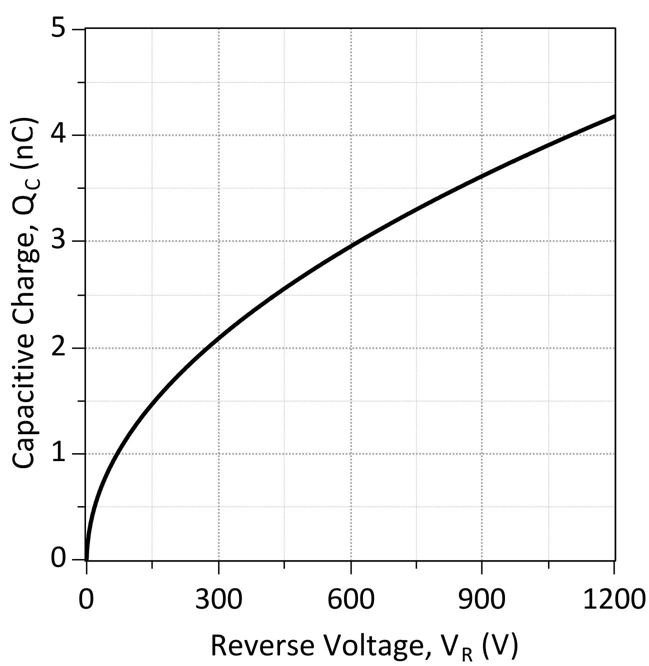
$I_F = f(T_C)$; $D = t_P/T$; $T_j = 175\ °C$

Figure 5: Current Derating Curves



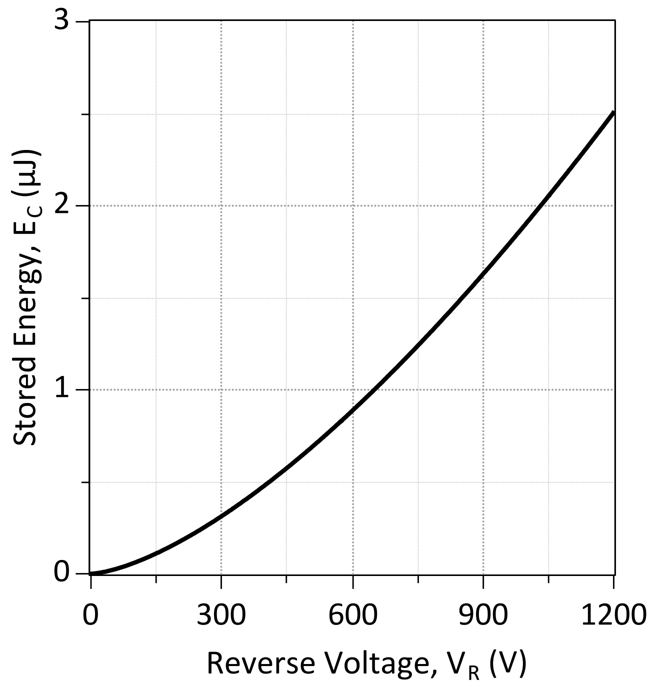
$C = f(V_R)$; f = 1 MHz

Figure 6: Typical Junction Capacitance vs Reverse Voltage Characteristics



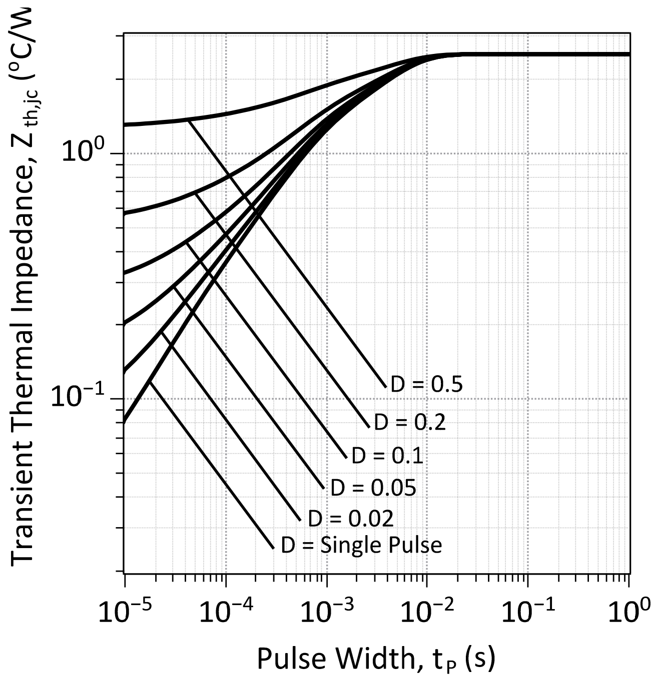
$Q_c = f(V_R)$; f = 1 MHz

Figure 7: Typical Capacitive Charge vs Reverse Voltage Characteristics



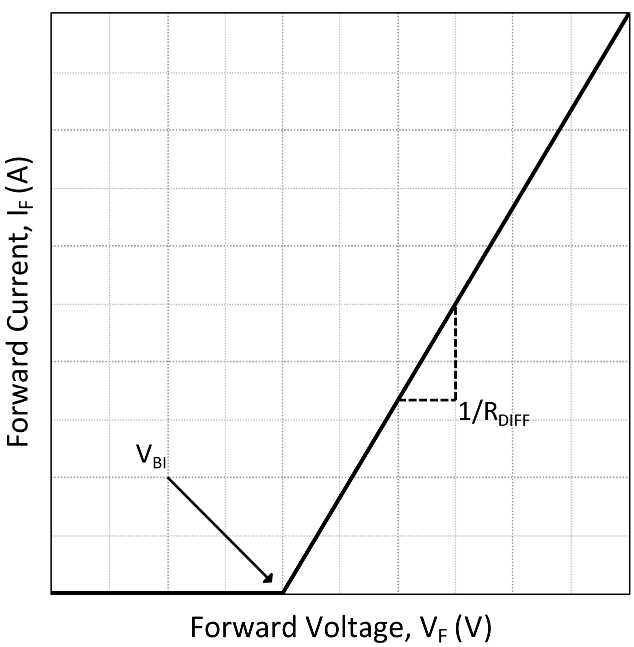
$E_C = f(V_R)$; f = 1 MHz

Figure 8: Typical Capacitive Energy vs Reverse Voltage Characteristics



$Z_{th,jc} = f(t_P, D)$; $D = t_P/T$

Figure 9: Transient Thermal Impedance



$I_F = f(V_F, T_j)$

$I_F = (V_F - V_{BI})/R_{DIFF}$ (A)

Built-In Voltage (V_{BI}):

$V_{BI}(T_j) = m*T_j + n$ (V),

m = -1.33e-03, n = 1.01

Differential Resistance (R_{DIFF}):

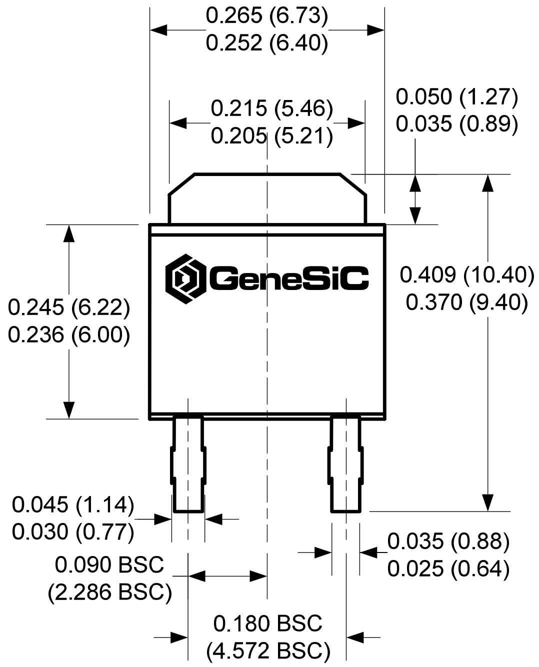
$R_{DIFF}(T_j) = a*T_j^2 + b*T_j + c$ (Ω);

a = 1.26e-05, b = 2.11e-03, c = 0.446

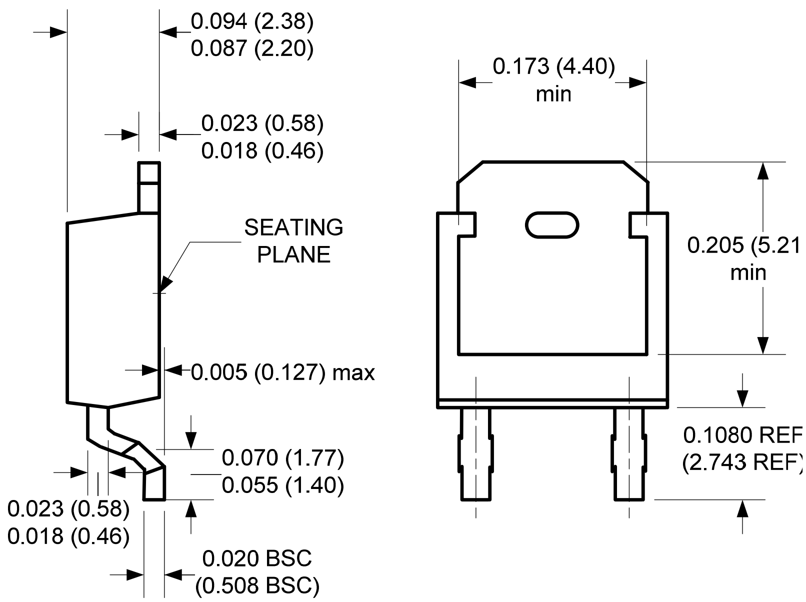
Figure 10: Forward Curve Model

Package Dimensions

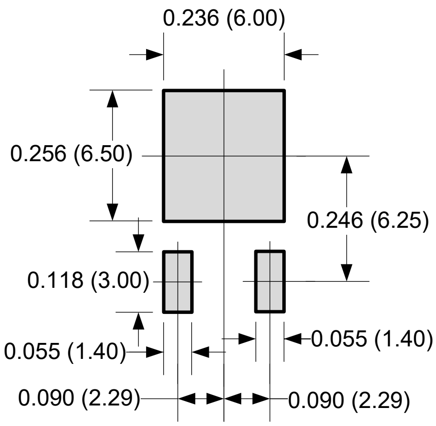
TO-252-2



Package Outline



Recommended Solder Pad Layout



NOTE

1. CONTROLLED DIMENSION IS INCH. DIMENSION IN BRACKET IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

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- SPICE Models: https://www.genesicsemi.com/schottky-mps
- Evaluation Boards: https://www.genesicsemi.com/technical-support
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Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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http://moschip.ru/get-element

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Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9